

Docket No.: 60188-652

**PATENT**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of	:	Customer Number: 20277
	:	
Masafumi KUBOTA, et al.	:	Confirmation Number:
	:	
Serial No.:	:	Group Art Unit:
	:	
Filed: September 16, 2003	:	Examiner: Unknown
	:	
For: METHOD FOR FABRICATING SEMICONDUCTOR DEVICE	:	

**INFORMATION DISCLOSURE STATEMENT**

Mail Stop IDS  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached form PTO-1449. It is respectfully requested that the documents be expressly considered during the prosecution of this application, and that the documents be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is being filed within three months of the U.S. filing date OR before the mailing date of a first Office Action on the merits. No certification or fee is required.


The relevance of each reference listed on attached Form 1449 is discussed in the present specification.

**Serial No.:**

Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

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**Date: September 16, 2003**

# INFORMATION DISCLOSURE CITATION IN AN APPLICATION

(PTO-1449)

 ATTY. DOCKET NO.  
60188-652

SERIAL NO.

 APPLICANT  
Masafumi KUBOTA, et al.

 FILING DATE  
September 16, 2003

GROUP

## U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code(s) of reference	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		US			
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## FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Code-Number + Kind- Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
						Yes	No

## OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
		Noriyuki Miyata et al., "Thermal Stability of $\text{HfO}_2/\text{Ultrathin-SiO}_2/\text{Si}$ Structures", EXTENDED ABSTRACTS OF THE 2002 INTERNATIONAL CONFERENCE ON SOLID STATE DEVICES AND MATERIALS, NAGOYA, pp478-479, 2002
		Shigenori Hayashi et al., "Preparation and characterization of high-k gate dielectric films by reactive sputtering", THE 60 <sup>TH</sup> SYMPO. SEMICONDUCTORS AND INTEGRATED CIRCUITS TECHNOLOGY, pp12-16

EXAMINER

DATE CONSIDERED

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.